

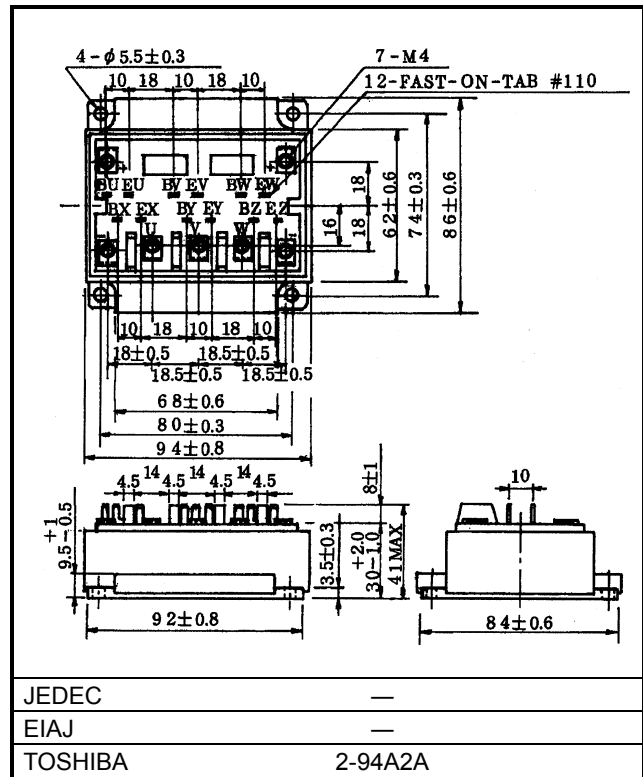
TOSHIBA GTR Module Silicon N Channel IGBT

# MG75J6ES50

High Power Switching Applications  
 Motor Control Applications

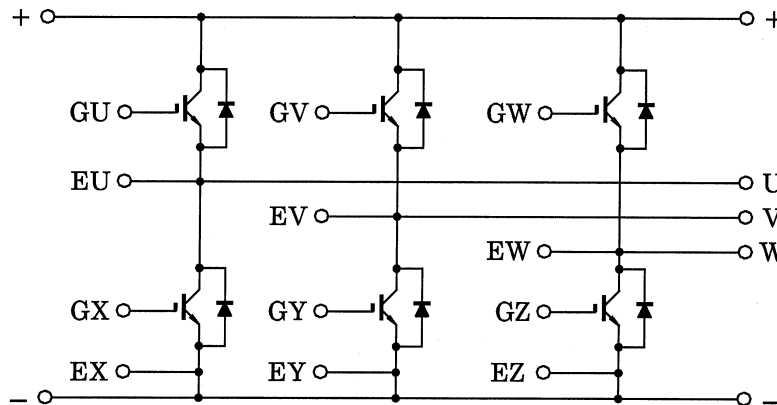
Unit: mm

- The electrodes are isolated from case.
- High input impedance.
- 6 IGBTs built into 1 package.
- Enhancement-mode.
- High speed :  $t_f = 0.30\mu s$  (Max) ( $I_C = 75A$ )  
 $t_{rr} = 0.15\mu s$  (Max) ( $I_F = 75A$ )
- Low saturation voltage  
 :  $V_{CE(sat)} = 2.70V$  (Max) ( $I_C = 75A$ )



Weight: 505g (Typ.)

## Equivalent Circuit



000707EAA1

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## Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit
Collector-emitter voltage		$V_{CES}$	600	V
Gate-emitter voltage		$V_{GES}$	$\pm 20$	V
Collector current	DC	$I_C$	75	A
	1ms	$I_{CP}$	150	
Forward current	DC	$I_F$	75	A
	1ms	$I_{FM}$	150	
Collector power dissipation (Tc = 25°C)		$P_C$	390	W
Junction temperature		$T_j$	150	°C
Storage temperature range		$T_{stg}$	-40 ~ 125	°C
Isolation voltage		$V_{isol}$	2500 (AC 1 min.)	V
Screw torque (Terminal / mounting)		—	2 / 3	N·m

## Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GES}$	$V_{GE} = \pm 20V, V_{CE} = 0$	—	—	$\pm 500$	nA
Collector cut-off current		$I_{CES}$	$V_{CE} = 600V, V_{GE} = 0$	—	—	1.0	mA
Gate-emitter cut-off voltage		$V_{GE (off)}$	$I_C = 7.5mA, V_{CE} = 5V$	5.0	7.0	8.0	V
Collector-emitter saturation voltage		$V_{CE (sat)}$	$I_C = 75A, V_{GE} = 15V$	—	2.10	2.70	V
Input capacitance		$C_{ies}$	$V_{CE} = 10V, V_{GE} = 0, f = 1MHz$	—	7100	—	pF
Switching time	Turn-on delay time	$t_{d (on)}$	Inductive load $V_{CC} = 300V$ $I_C = 75A$ $V_{GE} = \pm 15V$ $R_G = 18\Omega$  (Note 1)	—	0.08	0.16	$\mu s$
	Rise time	$t_r$		—	0.12	0.24	
	Turn-on time	$t_{on}$		—	0.40	0.80	
	Turn-off delay time	$t_{d (off)}$		—	0.20	0.40	
	Fall time	$t_f$		—	0.15	0.30	
	Turn-off time	$t_{off}$		—	0.50	1.00	
Forward voltage		$V_F$	$I_F = 75A, V_{GE} = 0$	—	2.10	2.80	V
Reverse recovery time		$t_{rr}$	$I_F = 75A, V_{GE} = -10V$ $di / dt = 100A / \mu s$	—	0.08	0.15	$\mu s$
Thermal resistance		$R_{th (j-c)}$	Transistor	—	—	0.32	°C / W
			Diode	—	—	0.69	

Note 1: Switching time test circuit & timing chert

